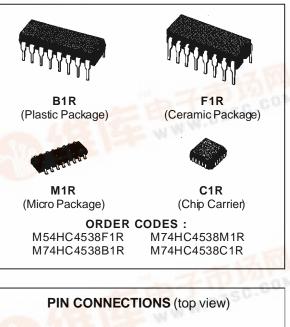




M54HC4538 M74HC4538

DUAL RETRIGGERABLE MONOSTABLE MULTIVIBRATOR

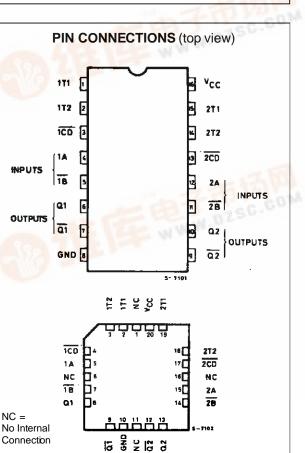
- HIGH SPEED t_{PD} = 25 ns (TYP.) AT V_{CC} = 5 V
 LOW POWER DISSIPATION STANDBY STATE I_{CC} = 4 μA (MAX.) AT T_A = 25 °C
- ACTIVE STATE ICC = 200 µA (TYP.) AT VCC = 5 V HIGH NOISE IMMUNITY
- V_{NIH} = V_{NIL} = 28 % V_{CC} (MIN.) ■ OUTPUT DRIVE CAPABILITY
- 10 LSTTL LOADS BALANCED PROPAGATION DELAYS
- TPLH = TPHL
- WIDE OUTPUT PULSE WIDTH RANGE twout = 120 ns ~ 60 s OVER AT Vcc = 4.5 V
- OUTPUT PULSE WIDTH INDEPENDENT FROM TRIGGER INPUT PULSE WIDTH
- PIN AND FUNCTION COMPATIBLE WITH 4538B



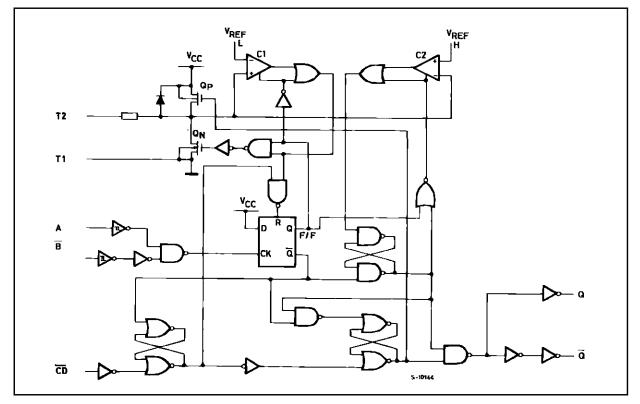
DESCRIPTION

The M54/74HC4538 is a high speed CMOS DUAL MONOSTABLE MULTIVIBRATOR fabricated in silicon gate C^2MOS technology. It has the same high speed performance of LSTTL combined with true CMOS low power consumption. Each multivibrator features both a negative, A, and a positive, B, edge triggered input, either of which can be used as an inhibit input. Also included is a clear input that when taken low resets the one shot. The monostable multivibrators are retriggerable. That is, they may be triggered reapeatedly while their outputs are generating a pulse and the pulse will be extended. Pulse width stability over a wide range of temperature and supply is achieved using linear CMOS techniques. The output pulse equation is simply : PW = 0.7 (R)(C) where PW is in seconds, R in Ohms, and C is in Farads.

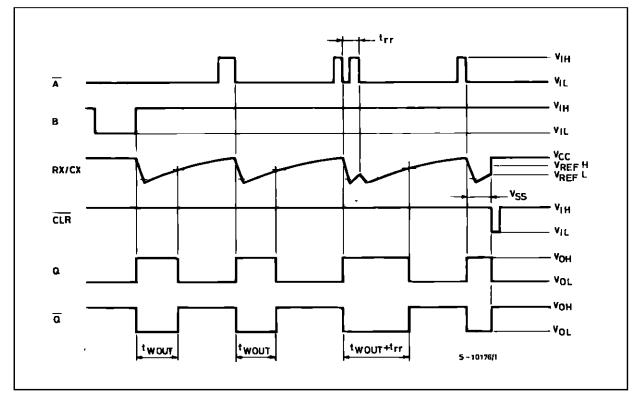
All pinputs are equipped with protection circuits against static discharge and transient excess voltage.



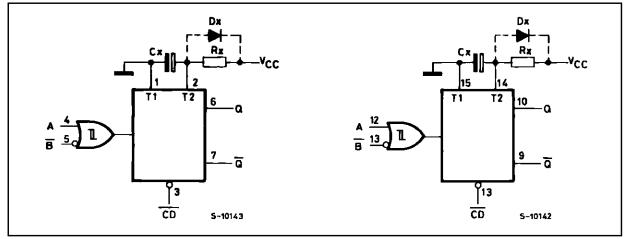
SYSTEM DIAGRAM



TIMING CHART



BLOCK DIAGRAM



Notes: 1. Cx, Rx, Dx are external components.

3. The external capacitor is charged to V_{CC} in the stand-by state, i.e. no trigger. When the supply voltage is turned off Cx is discharged mainly through an internal parasitic diode (see figures). If Cx is sufficiently large and V_{CC} decreases rapidy, there will be some possibility of damaging the I.C. with a surge current or latch-up. If the voltage supply filter capacitor is large enough and V_{CC} decrease slowly, the surge current is automatically limited and damage the I.C. is avoided. The maximum forward current of the parasitic diode is approximately 20 mA. In cases where Cx is large the time taken for the supply voltage to fall to 0.4 V_{CC} can be calculated as follows : $t_f \ge (V_{CC} - 0.7) \cdot Cx/20 \text{ mA}$

In cases where tr is too short an external champing diode is required to protect the I.C. from the surge current.

FUNCTIONAL DESCRIPTION

STAND-BY STATE

The external capacitor, Cx, is fully charged to V_{CC} in the stand-by state. Hence, before triggering, transistor Qp and Qn (connected to the Rx/Cx node) are both turned off. The two comparators that control the timing and the two reference voltage sources stop operating. The total supply current is therefore only leakage current.

TRIGGER OPERATION

Triggering occurs when :

1 st) A is "low" and \overline{B} has a falling edge ;

2 nd) \overline{B} is "high" and A has a rising edge;

After the multivibrator has been retriggered comparator C1 and C2 start operating and Qn is turned on. Cx then discharges through Qn. The voltage at the node Rx/Cx external falls.

When it reaches V_{REFL} the output of comparator C1 becomes low. This in turn resets the flip-flop and Qn is turned off.

At this point C1 stops functioning but C2 continues to operate. The voltage at R/C external begins to rise with a time constant set by the external components Rx, Cx.

Triggering the multivibrator causes Q to go high after internal delay due to the flip-flop and the gate. Q remains high until the voltage at R/C external rises again to V_{REFH}. At this point C2 output goes low and G goes low. C2 stops operating. That means that after triggering when the voltage at R/C external returns to V_{REFH} the multivibrator has returned to its MONOSTABLE STATE. In the case where Rx • Cx are large enough and the discharge time of the capacitor and the delay time in the I.C. can be ignored, the width of the output pulse tw (out) is as follows : $t_{W(OUT)} = 0.72 \text{ Cx} \cdot \text{Rx}$

RE-TRIGGER OPERATION

When a second trigger pulse follows the first its effect will depend on the state of the multivibrator. If the capacitor Cx is being charged the voltage level of Rx/Cx external falls to V_{REFL} again and Q remains high i.e. the retrigger pulse arrives in a time shorter than the period Rx • Cx seconds, the capacitor charging time constant. If the second trigger pulse is very close to the initial trigger pulse it is ineffective; i.e., the second trigger must arrive in the capacitor discharge cycle to be ineffective.

Hence the minimum time for a second trigger to be effective, trr (Min.) depends on V_{CC} and Cx.

^{2.} Dx is a clamping diode.

FUNCTIONAL DESCRIPTION (continued)

RESET OPERATION

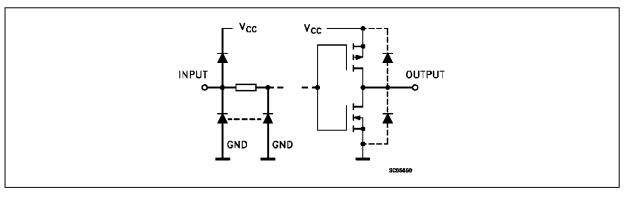
 $\overline{\text{CD}}$ is normally high. If $\overline{\text{CD}}$ is low, the trigger is not effective because Q output goes low and trigger control flip-flop is reset.

Also transistor Op is turned <u>on</u> and Cx is charged quicky to V_{CC} . This means if CD input goes low, the IC becomes waiting state both in operating and non operating state.

TRUTH TABLE

INPUTS			OUTI	PUTS	NOTE
Α	B	CD	Q	a	NOTE
	Н	Н			OUTPUT ENABLE
Х	L	Н	L	Н	INHIBIT
Н	Х	Н	L	Н	INHIBIT
L		Н			OUTPUT ENABLE
Х	Х	L	L H		INHIBIT

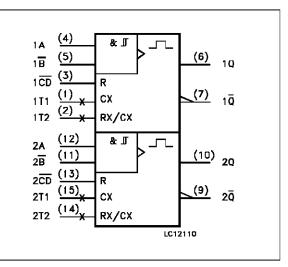
INPUT AND OUTPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 15	1T1, 2T1	External Capacitor Connections
2, 14	1T2, 2T2	External Resistor/Capacitor Connections
3, 13	1CD, 2CD	Direct Reset Inputs (Active LOW)
4, 12	1A, 2A	Trigger Inputs (LOW to HIGH, Edge-Triggered)
5, 11	1B, 2B	Trigger Inputs (HIGH to LOW, Edge-Triggered)
6, 10	Q1, Q2	Pulse Outputs
7, 9	$\overline{Q}1, \overline{Q}2$	Complementary Pulse Outputs
8	GND	Ground (0V)
16	V _{CC}	Positive Supply Voltage

IEC LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
Vcc	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{ОК}	DC Output Diode Current	± 20	mA
lo	DC Output Source Sink Current Per Output Pin	± 25	mA
Icc or I _{GND}	DC V _{CC} or Ground Current	± 50	mA
PD	Power Dissipation	500 (*)	mW
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. (*) 500 mW: \cong 65 °C derate to 300 mW by 10mW/°C: 65 °C to 85 °C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit	
V _{CC}	Supply Voltage	2 to 6	V	
VI	Input Voltage	0 to V _{CC}	V	
Vo	Output Voltage		0 to V _{CC}	V
T _{op}	Operating Temperature: M54HC Series M74HC Series		-55 to +125 -40 to +85	ဂီ ဂီ
t _r , t _f	Input Rise and Fall Time (CLR only)	$V_{CC} = 2 V$	0 to 1000	
		Vcc = 4.5 V	0 to 500	ns
		$V_{CC} = 6 V$	0 to 400	
Cx	External Capacitor		NO LIMITATION (*)	
Rx	External Resistor	$V_{CC} \le 3 V$	5K to 1M (*)	Ω
		V _{CC} > 3 V	1K to 1M (*)	22

(*) The maximum allowable values of Cx and Rx are a function of leakage of capacitor Cx, the leakage of device and leakage due to the board layout and surface resistance. Susceptibility to externally induced noise may occur for $Rx > 1M\Omega$

DC SPECIFICATIONS

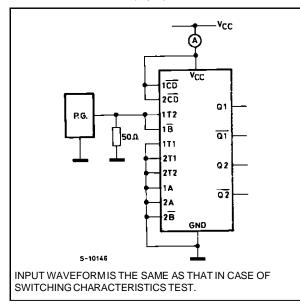
		Test Conditions			Value							
Symbol	Parameter	V _{CC} (V)		$T_A = 25 \ ^{\circ}C$ 54HC and 74HC			-40 to 85 °C 74HC		-55 to 125 °C 54HC		Unit	
		(v)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
VIH	High Level Input	2.0			1.5			1.5		1.5		
	Voltage	4.5			3.15			3.15		3.15		V
		6.0			4.2			4.2		4.2		
VIL	Low Level Input	2.0					0.5		0.5		0.5	
	Voltage	4.5					1.35		1.35		1.35	5 V
		6.0					1.8		1.8		1.8	
Voh	High Level	2.0	Vi =		1.9	2.0		1.9		1.9		
	Output Voltage	4.5	VI – VIH	I _O =-20 μΑ	4.4	4.5		4.4		4.4		.,
		6.0	or		5.9	6.0		5.9		5.9		V
		4.5	VIL	lo=-4.0 mA	4.18	4.31		4.13		4.10		
		6.0		I ₀ =-5.2 mA	5.68	5.8		5.63		5.60		
Vol	Low Level Output	2.0	VI =			0.0	0.1		0.1		0.1	
	Voltage	4.5	VI – VIH	I _O = 20 μA		0.0	0.1		0.1		0.1	
		6.0	or			0.0	0.1		0.1		0.1	V
		4.5	Vı∟	I _O = 4.0 mA		0.17	0.26		0.37		0.40	
		6.0		l ₀ = 5.2 mA		0.18	0.26		0.37		0.40	
lı	Input Leakage Current	6.0	VI = '	V _{CC} or GND			±0.1		±1		±1	μA
I _I	Input Leakage Current	6.0		√ _{CC} or GND ext/Cext			±0.1		±1		±1	μΑ
I _{CC}	Quiescent Supply Current	6.0	V1 = 1	V _{CC} or GND			4		40		80	μΑ
Icc	Quiescent Supply	2.0	V1 = 1	V _{CC} or GND		40	120		160			μΑ
	Current	4.5		ns 2, 14		0.2	0.3		0.4			mA
		6.0	Vi	$= V_{CC}/2$		0.3	0.6		0.8			mA

		Т	est Con	ditions	Value								
Symbol	Parameter	Vcc			_A = 25 ^C C and 7			85 °C HC	-55 to 125 °C 54HC		Unit		
		(V)			Min.	Тур.	Max.	Min.	Max.	Min.	Max.		
t _{TLH}	Output Transition	2.0				30	75		95		110		
t _{THL}	Time	4.5]			8	15		19		22	ns	
		6.0]			7	13		16		19		
t _{PLH}	Propagation	2.0				120	250		315		375		
t PHL	Delay Time	4.5				30	50		63		75	ns	
$(A, \overline{B} - Q, \overline{Q})$	(A, B - Q, Q)	6.0				25	43		54		64		
t _{PLH}	Propagation	2.0				100	195		245		295		
t _{PHL}	Delay Time	4.5				25	39		49		59	ns	
	(CD - Q, Q)	6.0				20	33		42		50		
twout	Output Pulse	2.0		$R_X = 5K\Omega$		540	1200		1500		1800		
	Width	4.5	$C_X = 0$	$R_X = 1K\Omega$		180	250		320		375	ns	
		6.0		$R_X = 1K\Omega$		150	200		260		320		
		2.0		0.01 µF	70	83	96	70	96	70	96		
		4.5		= 10KΩ	69	77	85	69	85	69	85	μs	
		6.0			69	77	85	69	85	69	85		
		2.0		= 0.1 μF	0.67	0.75	0.83	0.67	0.83	0.67	0.9		
		4.5		= 10KΩ	0.67	0.73	0.77	0.67	0.77	0.67	0.8	ms	
		6.0		_	0.67	0.73	0.77	0.67	0.77	0.67	0.8		
Δt _{WOUT}	Output Pulse Width Error Between Circuits (In same pack)					±1						%	
t _{W(H)}	Minimum Pulse	2.0				30	75		95		110		
t _{W(L)}	Width	4.5				8	15		19		22	ns	
	(CLOCK)	6.0	1			7	13		16		19		
t _{W(L)}	Minimum Pulse	2.0				30	75		95		110		
.,	Width	4.5]			8	15		19		22	ns	
	(CLEAR)	6.0]			7	13		16		19		
t _{REM}	Minimum Clear	2.0				0	15		15		20		
	Removal Time	4.5]			0	5		5		7	ns	
		6.0				0	5		5				
t _s	Minimum	2.0		= 0.1 μF		380					6		
	Retrigger Time	4.5		= 1KΩ		92						ns	
		6.0				72							
		2.0	С _У –	0.01 μF		6							
		4.5		= 1KΩ		1.4						μs	
		6.0				1.2							
CIN	Input Capacitance					5	10		10		10	pF	
C _{PD} (*)	Power Dissipation Capacitance					70						pF	

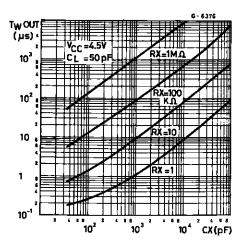
AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 6 \text{ ns}$)

(*) C_{PD} is defined as the value of the IC's internal equivalent capaditance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operting current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}' \bullet Duty/100 + I_{CC}/2$ (per circuit) ($I_{CC}' = Active Supply Current$) (Duty = %))

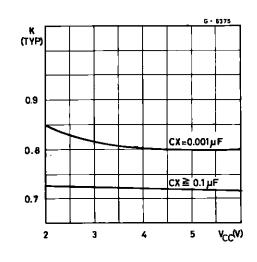
TEST CIRCUIT Icc (Opr.)



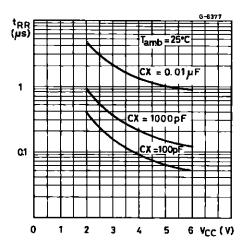
twour - Cx Characteristics (Typ).



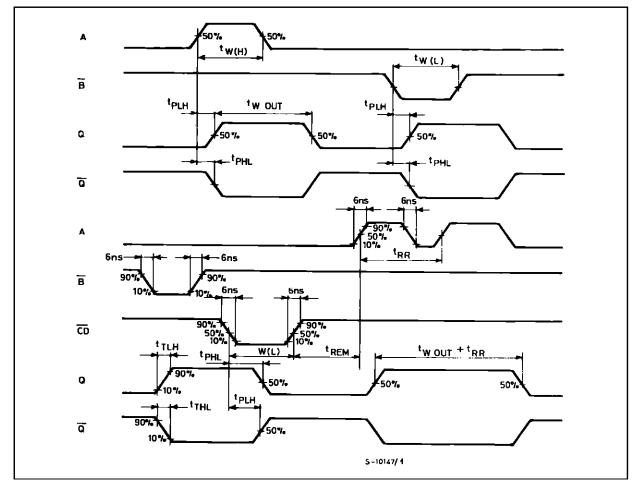
Output Pulse Width Constant K = Supply Voltage.



trr - V_{CC} Characteristics (Typ).

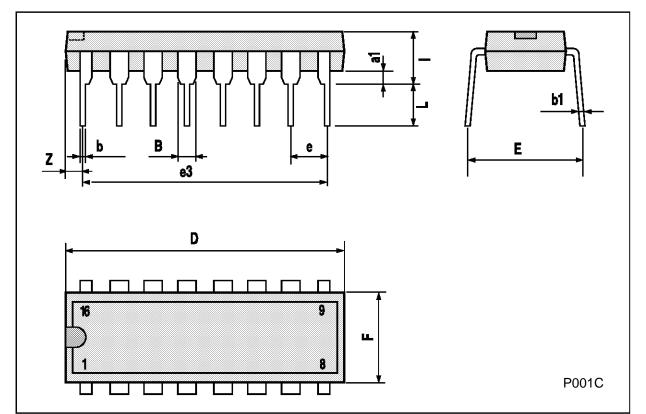


SWITCHING CHARACTERISTICS TEST WAVEFORM



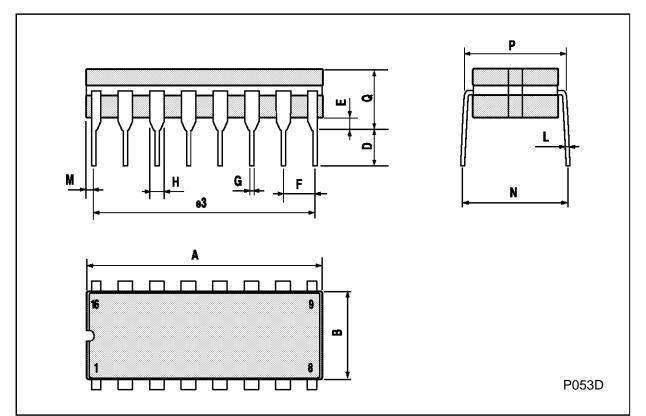
DIM.		mm		inch				
Dini	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
a1	0.51			0.020				
В	0.77		1.65	0.030		0.065		
b		0.5			0.020			
b1		0.25			0.010			
D			20			0.787		
E		8.5			0.335			
е		2.54			0.100			
e3		17.78			0.700			
F			7.1			0.280		
I			5.1			0.201		
L		3.3			0.130			
Z			1.27			0.050		

Plastic DIP16 (0.25) MECHANICAL DATA



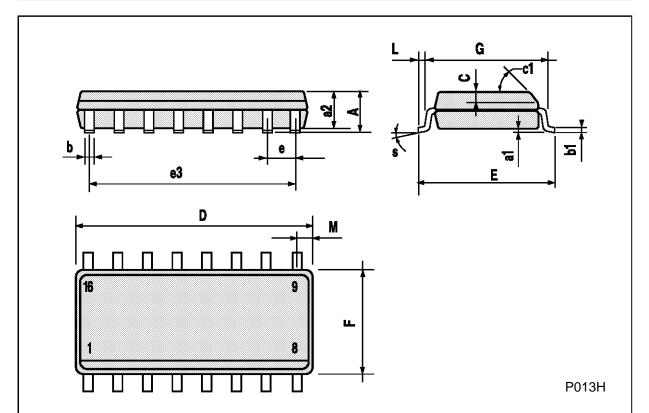
DIM.		mm		inch				
Diwi.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.		
А			20			0.787		
В			7			0.276		
D		3.3			0.130			
E	0.38			0.015				
e3		17.78			0.700			
F	2.29		2.79	0.090		0.110		
G	0.4		0.55	0.016		0.022		
н	1.17		1.52	0.046		0.060		
L	0.22		0.31	0.009		0.012		
М	0.51		1.27	0.020		0.050		
Ν			10.3			0.406		
Р	7.8		8.05	0.307		0.317		
Q			5.08			0.200		

Ceramic DIP16/1 MECHANICAL DATA



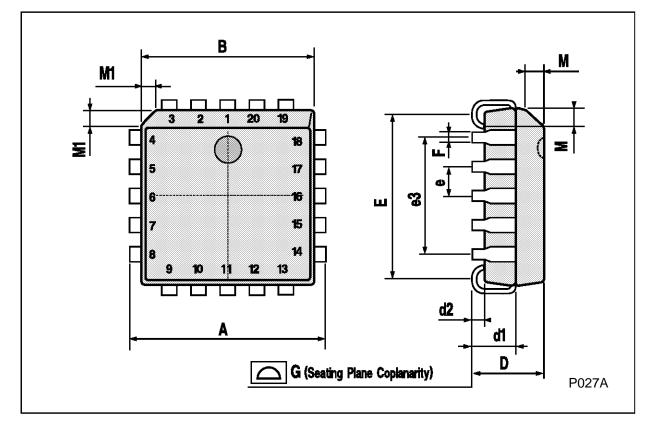
DIM.		mm			inch					
DINI.	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.				
А			1.75			0.068				
a1	0.1		0.2	0.004		0.007				
a2			1.65			0.064				
b	0.35		0.46	0.013		0.018				
b1	0.19		0.25	0.007		0.010				
С		0.5			0.019					
c1			45°	(typ.)						
D	9.8		10	0.385		0.393				
Е	5.8		6.2	0.228		0.244				
е		1.27			0.050					
e3		8.89			0.350					
F	3.8		4.0	0.149		0.157				
G	4.6		5.3	0.181		0.208				
L	0.5		1.27	0.019		0.050				
М			0.62			0.024				
S		8° (max.)								

SO16 (Narrow) MECHANICAL DATA



DIM.		mm		inch			
Dim	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	
А	9.78		10.03	0.385		0.395	
В	8.89		9.04	0.350		0.356	
D	4.2		4.57	0.165		0.180	
d1		2.54			0.100		
d2		0.56			0.022		
E	7.37		8.38	0.290		0.330	
е		1.27			0.050		
e3		5.08			0.200		
F		0.38			0.015		
G			0.101			0.004	
М		1.27			0.050		
M1		1.14			0.045		

PLCC20 MECHANICAL DATA



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